٠<u>٠</u>

Substitute for form 1449A/PTO

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 2

1		Complete if Known	
	Application Number	10/715,971	
	Filing Date	November 17, 2003	
	First Named Inventor	Shahriar Ahmed	
	Art Unit	2812	
_	Examiner Name		
	Attorney Docket Number	42P17289	

			U.S. PATE	NT DOCUMENTS	
Examiner Initials*	Cite No.1	Document Number  Number - Kind Code <sup>*</sup> (if known)	Publication Date or Issue Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
TSY		US-5,250,448	10-05-1993	Hamasaki et al.	
TAP		US-2002/0132438 A1	09-19-2002	Dunn et al.	
130		US-2003/0136975 A1	07-24-2003	Coolbaugh et al.	
108		US-2002/027232 A1	03-03-2004	Shigematsu et al.	:
W		US-6,541,336 B1	04-01-2003	Cantell et al.	
TO		US-2002/197783 A1	12-26-2002	Ahlgren et al.	
		US-			
	<u> </u>	US-			
		US-			

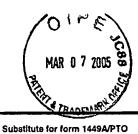
		FOF	REIGN PATEN	IT DOCUMENTS		
Examiner	Cite	Foreign Patent Document			Pages, Columns, Lines,	т.
Initials*	No.'	Country Code* - Number* - Kind Code* (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Where Relevant Passages or Relevant Figures Appear	
TSP		DE 101 04 776 A1	08-22-2002	Infineon Technologies AG		
10		EP 1 489 662 A2	12-22-2004	Samsung Electronics Co.		
188		EP 1 394 861 A3	03-03-2004	Chartered Semiconductor Mfg.		
						L
						<u>                                     </u>
						ļ
						_
						į

Examiner	Date	3/07/05
Signature	Considered	3/2//03

'Applicant's unique citation designation number (optional). 'See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. 'Enter Office that Issued the document, by the two-letter code (WIPO Standard ST.3). 'For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. 'Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. 'Applicant is to place a check mark here if English language Translation is attached.

Based on PTO/SB/08A (08-03) as modified by Blakely, Solokolf, Taylor & Zafman (wir) 08/11/2003.

<sup>\*</sup>Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.



Sheet

INFORMATION DISCLOSURE

2

STATEMENT BY APPLICANT

of

2

Complete if Known

Application Number 10/715,971

Filing Date November 17, 2003

First Named Inventor Shahriar Ahmed

Art Unit 2812

Examiner Name

Attorney Docket Number 42P17289

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.'	Include name of the author (in CAPITAL LETTERS), title of the stricle (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Ť
TSP		Ida, Minoru et al., "Enhancement of fmax in InP/InGaAs HBT's by Selective MOCVD Growth of Heavily-Doped Extrinsic Base Regions," IEEE Trans on Elect Devices, Vol. 43, No. 11, Nov 1996, pgs. 1812-1817.	
	<del></del>	·	
		,	
	•••••		
	······································		

|--|

<sup>\*</sup>Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.